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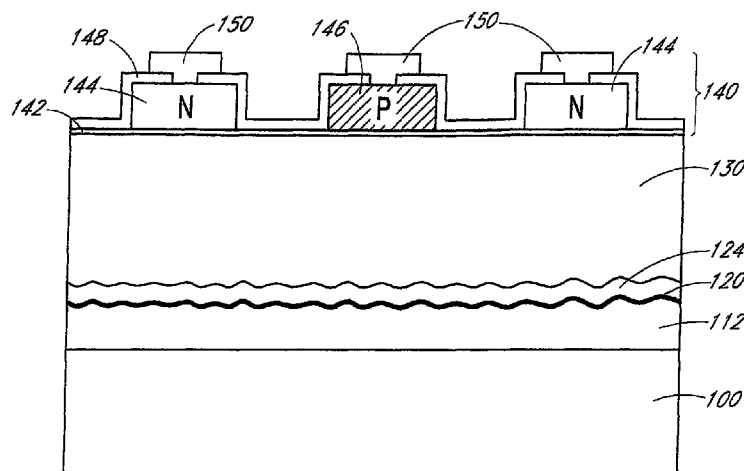


FIG. 8

(57) Abstract: A method of fabricating a solar cell is disclosed. The method includes the steps of forming a sacrificial layer (112) on a silicon substrate (100), forming a doped silicon layer (120) atop the sacrificial substrate, forming a silicon film (130) atop the doped silicon layer (120), forming a plurality of interdigitated contacts (144, 146) on the silicon film (130), contacting each of the plurality of interdigitated contacts (144, 146) with a metal contact (150), and removing the sacrificial layer (112).